## NSN 5962-01-391-1182

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View Online at https://aerobasegroup.com/nsn/5962-01-391-1182

view Offilite at https://defobasegroup.com/hsr//0502-01-051-1102
Body Length:
1.060 inches
Body Width:
Between 0.220 inches and 0.320 inches
Body Height:
0.185 inches
Maximum Power Dissipation Rating:
2.0 milliwatts
Operating Tempurature Range:
-55.0/+125.0 degrees celsius
Storage Tempurature Range:
-65.0/+125.0 degrees celsius
End Application:
Pacer dawn
Features Provided:
Monolithic and bipolar and programmable
Inclosure Material:
Ceramic
Inclosure Configuration:
Dual-in-line Dual-in-line
Output Logic Form:
Transistor-transistor logic
Input Circuit Pattern:
16 input
Criticality Code Justification:
Feat
Case Outline Source And Designator:
D-8 mil-m-38510
Terminal Surface Treatment:
Solder
Voltage Rating And Type Per Characteristic:
12.0 volts power source
Time Rating Per Chacteristic:
30.00 nanoseconds propagation delay time, low to high level output and 30.00 nanoseconds propagation delay time, high to low level
output
Memory Device Type:
Pal
Special Features:
Esd, software file no: 8912782-2-701, using module i/o-8905870-511 and location u5

81349-mil-m-38510 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain

### **Terminal Type And Quantity:**

**Test Data Document:** 

environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.).

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N/a

**Unit Of Measure:** 

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Demilitarization:

No

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